CEP260N10S/CEB260N10S

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

■ 100V, 256A, TO-263 $R_{DS(ON)\ typ}$ = 1.8mΩ @V_{GS} = 10V

TO-220 $R_{DS(ON)\ typ}$ = 2.0mΩ @V_{GS} = 10V

■ Super high dense cell design for extremely low $R_{DS(ON)}$.

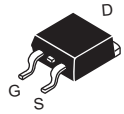
■ High power and current handing capability.

■ RoHS compliant.

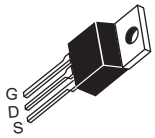
■ TO-220 & TO-263 package.

Applications

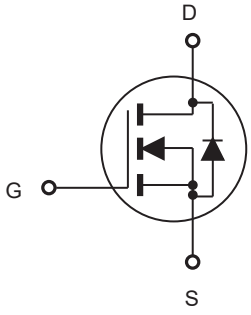
■ Battery protection,UPS.



CEB SERIES
TO-263(DD-PAK)



CEP SERIES
TO-220



ABSOLUTE MAXIMUM RATINGS T_C = 25°C unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous@ T_C = 25°C	I_D	256	A
@ T_C = 100°C		180	A
Drain Current-Pulsed [a]	I_{DM}	1024	A
Maximum Power Dissipation @ T_C = 25°C	P_D	283	W
- Derate above 25°C		1.8	W/°C
Single Pulsed Avalanche Energy [d]	E_{AS}	720	mJ
Single Pulsed Avalanche Current [d]	I_{AS}	60	A
Operating and Store Temperature Range	T_J,T_{stg}	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.53	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

Electrical Characteristics T_C = 25°C unless otherwise noted

Parameter	Symbol	Test Condition		Min	Typ	Max	Units
Off Characteristics							
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I_D = 250μA		100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100V, V_{GS} = 0V				1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	V_{GS} = 20V, V_{DS} = 0V				100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	V_{GS} = -20V, V_{DS} = 0V				-100	nA
On Characteristics [b]							
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 250μA		2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 20A	TO-263		1.8	2.2	mΩ
			TO-220		2.0	2.4	mΩ
		V_{GS} = 10V, I_D = 100A	TO-263		1.9	2.3	mΩ
			TO-220		2.1	2.5	mΩ
Gate input resistance	R_g	f=1MHz,open Drain			2.2		Ω
Dynamic Characteristics [c]							
Input Capacitance	C_{iss}	V_{DS} = 50V, V_{GS} = 0V, f = 1.0 MHz			4570		pF
Output Capacitance	C_{oss}				1250		pF
Reverse Transfer Capacitance	C_{rss}				70		pF
Switching Characteristics [c]							
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 50V, I_D = 20A, V_{GS} =10V, R_{GEN} = 10Ω			50		ns
Turn-On Rise Time	t_r				88		ns
Turn-Off Delay Time	$t_{d(off)}$				167		ns
Turn-Off Fall Time	t_f				122		ns
Total Gate Charge	Q_g	V_{DS} = 50V, I_D = 20A, V_{GS} = 10V			155		nC
Gate-Source Charge	Q_{gs}				29.5		nC
Gate-Drain Charge	Q_{gd}				57		nC
Drain-Source Diode Characteristics and Maximun Ratings							
Drain-Source Diode Forward Current	I_S					267	A
Drain-Source Diode Forward Voltage [b]	V_{SD}	V_{GS} = 0V, I_S = 20A				1.2	V
Reverse Recovery Time	T_{rr}	I_F = 20A, di /dt = 500A/us			80		ns
Reverse Recovery Charge	Q_{rr}				625		nC

Notes :
a.Repetitive Rating : Pulse width limited by maximum junction temperature
b.Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
c.Guaranteed by design, not subject to production testing.
d.L = 0.4mH, I_{AS} = 60A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25 C

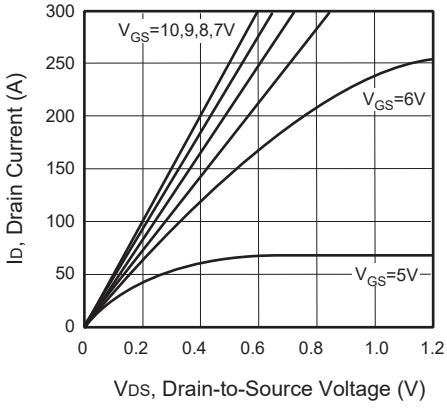


Figure 1. Output Characteristics

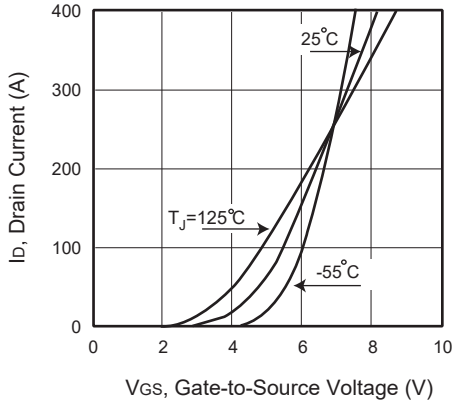


Figure 2. Transfer Characteristics

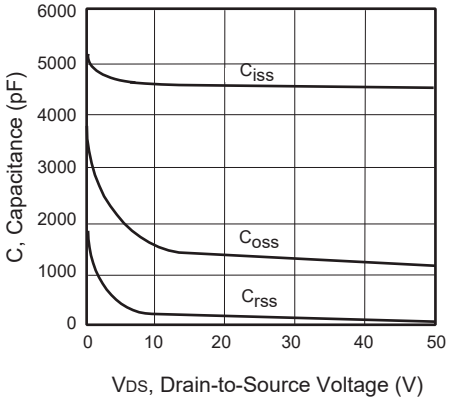


Figure 3. Capacitance

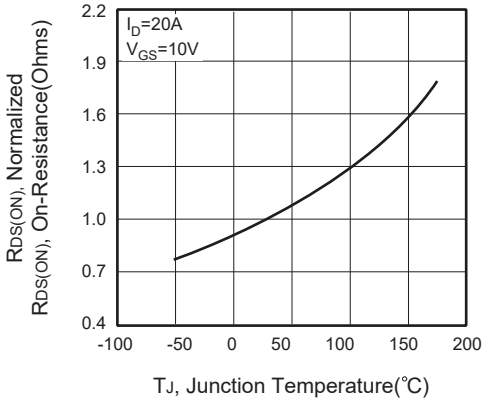


Figure 4. On-Resistance Variation with Temperature

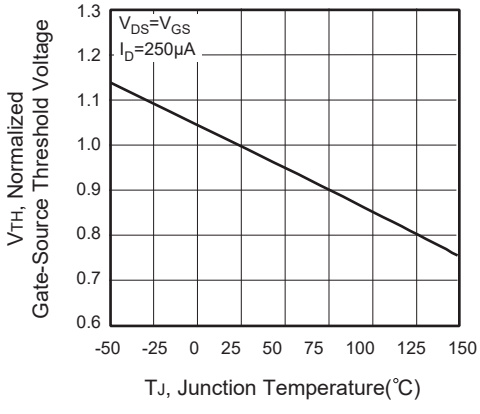


Figure 5. Gate Threshold Variation with Temperature

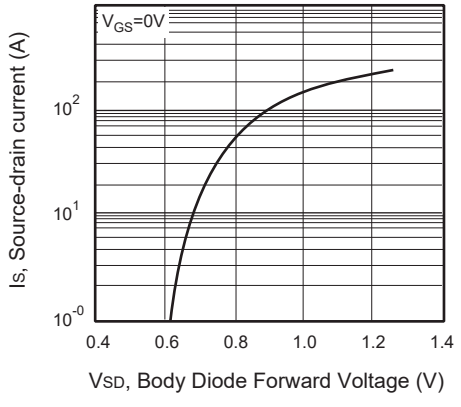


Figure 6. Body Diode Forward Voltage Variation with Source Current

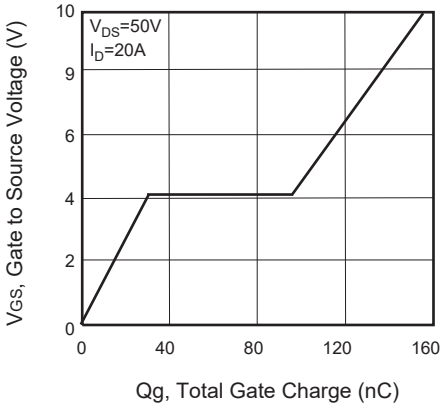


Figure 7. Gate Charge

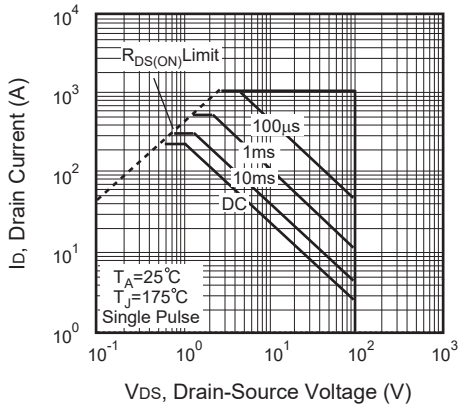


Figure 8. Maximum Safe Operating Area

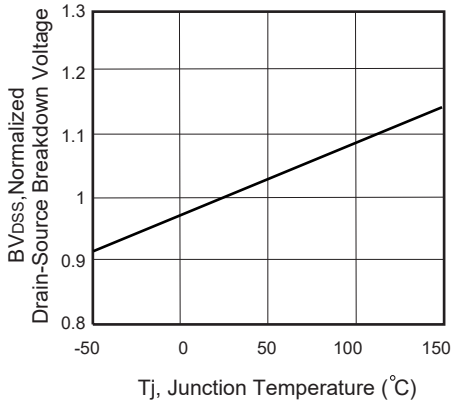


Figure 9. Breakdown Voltage Variation VS Temperature

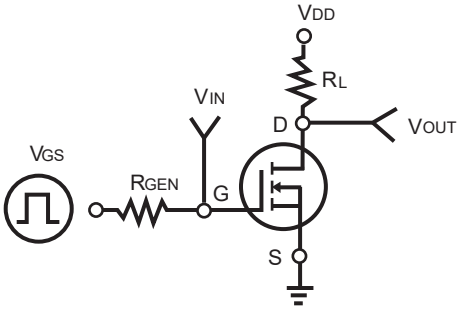


Figure 10. Switching Test Circuit

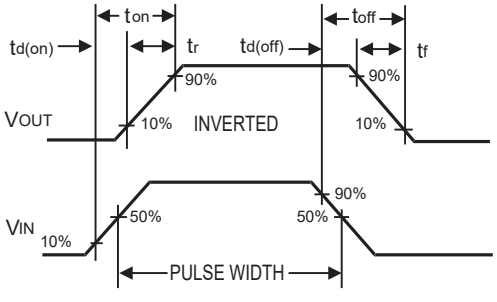


Figure 11. Switching Waveforms

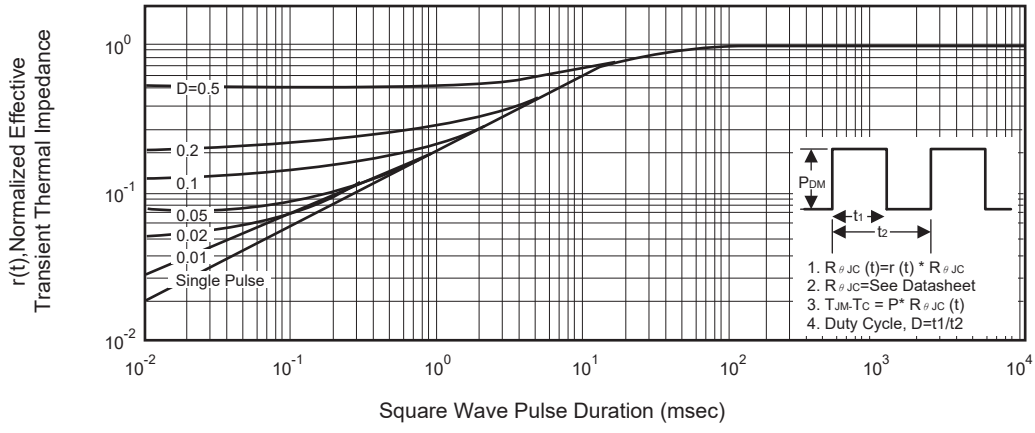


Figure 12. Normalized Thermal Transient Impedance Curve